

Update on electron transparency simulation and comparison to ExMe Studies

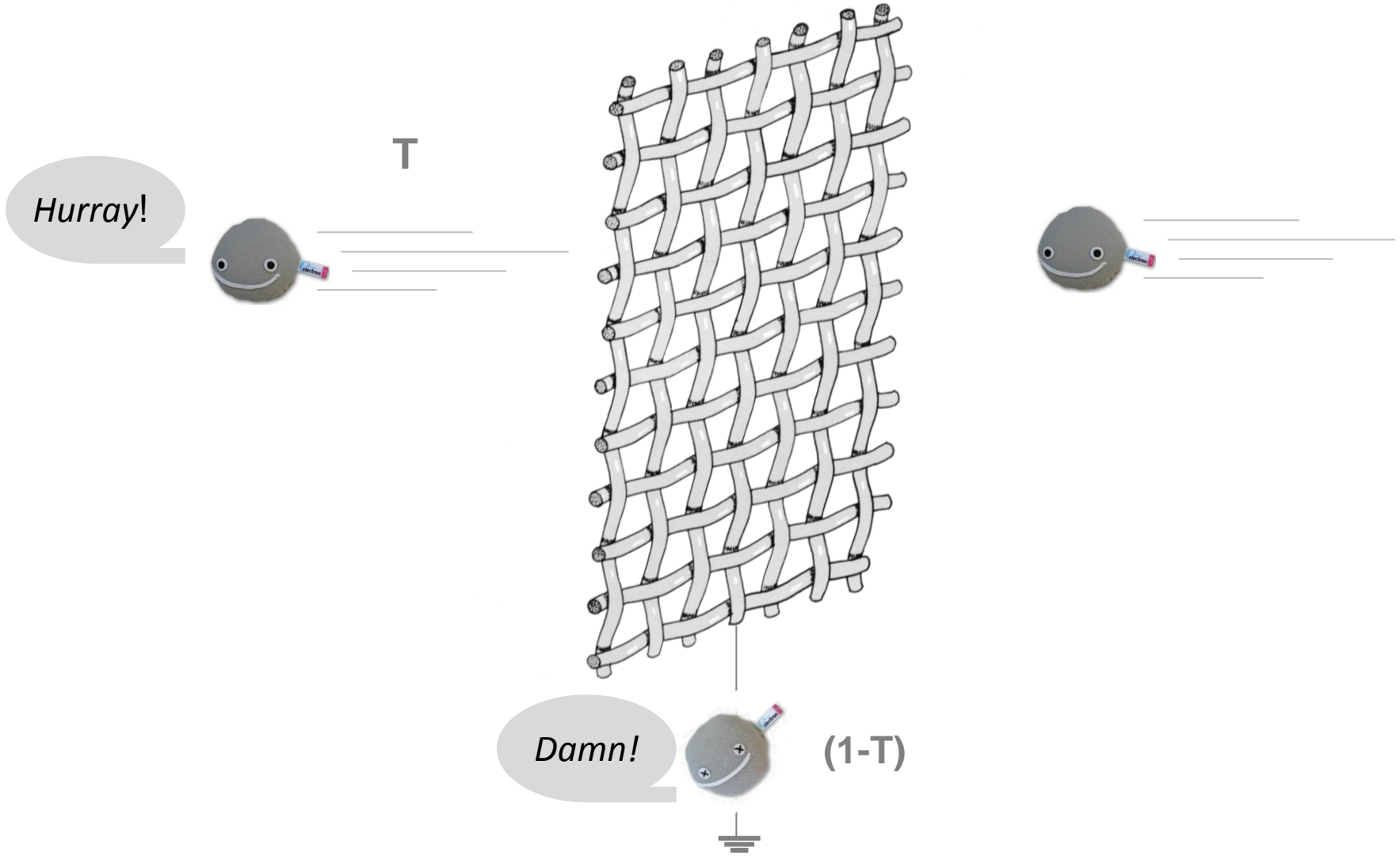
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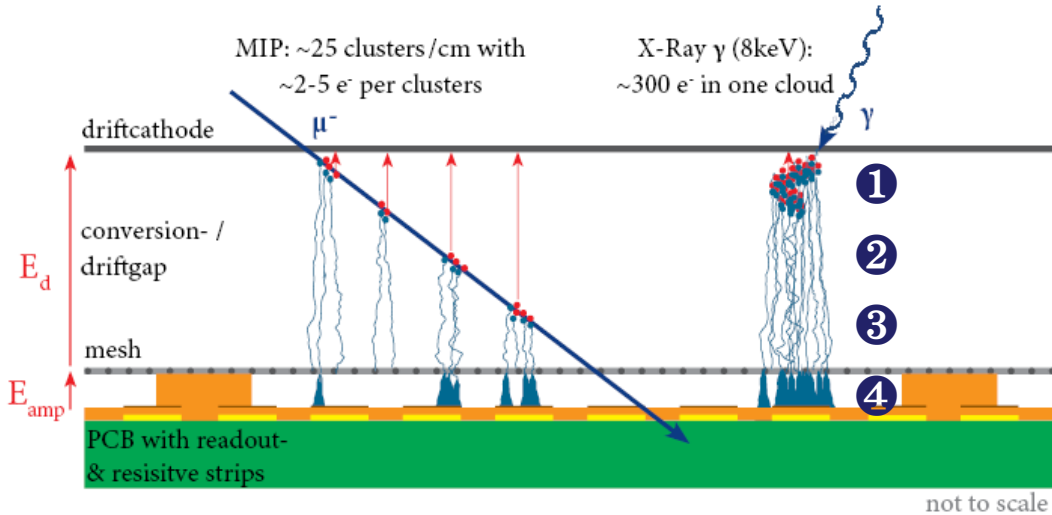
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March 19th 2015

RD51 Collaboration Meeting - CERN



Which *gas-processes* contribute to the signal formation a Micromegas?



- 1 Primary ionization / conversion ✓
→ Typical energy loss tables (e.g. HEED)
 - 2 Electron drift (diffusion, attachment...) ✓
→ cross section databases (e.g. Magboltz, GARFIELD)
 - 3 Electron losses at the mesh ✗
 - 4 Electron amplification ✓
→ including additional e⁻ production mechanisms
(*Understanding avalanches in a Micromegas from single-electron response measurement*, NIM A 772 - 2015)
- (+ 5 signal capture, readout, amplification etc.)

3: Electron transparency of the mesh $T = \frac{\#e^- \text{ passing through the mesh}}{\#e^- \text{ approaching the mesh}}$, depends on

➤ mesh geometry: wire-diameter, mesh -opening width -> open area, mesh thickness & structure...

➤ approaching behavior of the electrons:

gas
(composition, temperature, pressure)

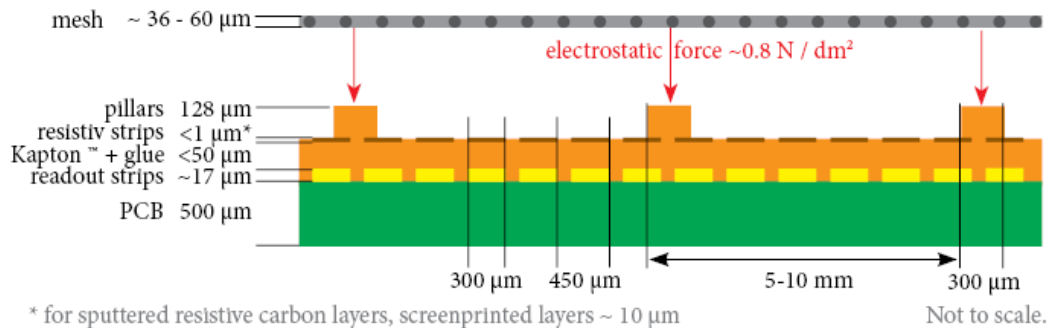
&

electrical field
(geometry + voltages on drift, mesh & readout)

To study different meshes under ideally comparable conditions we designed and build a Micromegas with an **exchangeable mesh**:

→ Presented during IWAD & 14th RD51 Meeting
(2014, Kolkata)

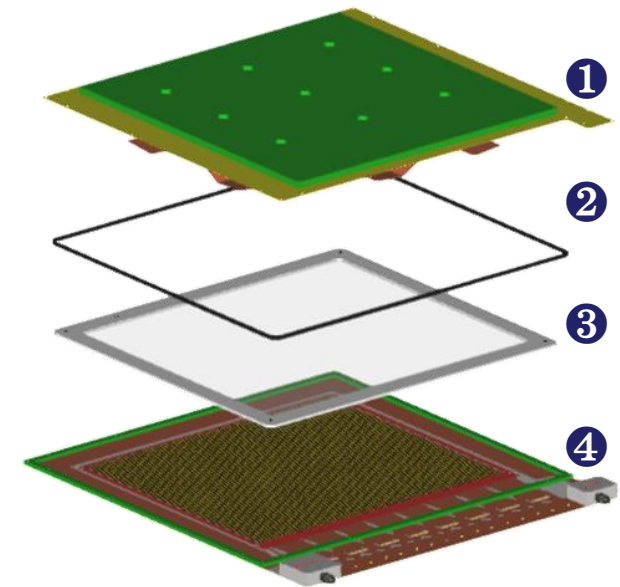
- Following the **floating mesh** concept
(as for seen for ATLAS NSW Micromegas)



- **Independent mesh frames** allow easy mesh exchange
(ATLAS NSW: mesh will be fixed on the drift panel)

→ Most detector **inherent parameters** (amplification- and drift gap thickness, readout surface etc.) are kept constant and allow direct mesh comparison

Schematic view of the ExMe1 components



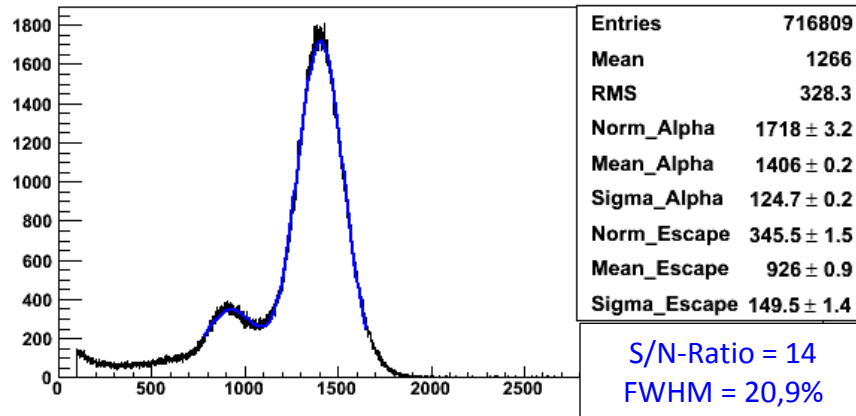
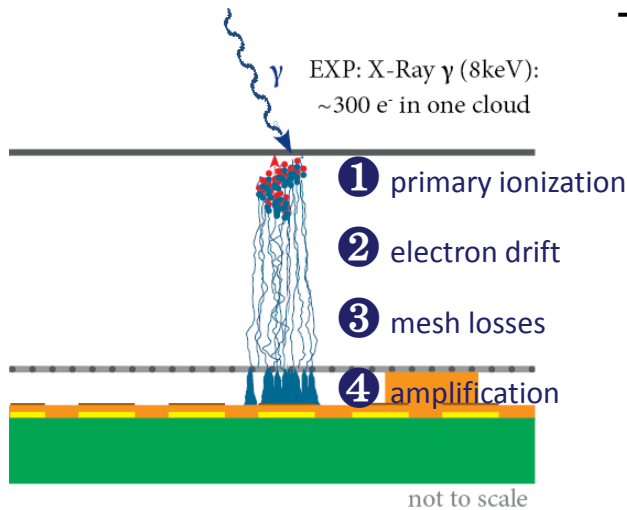
- ① Drift panel (stiff-back, internal gas lines, drift cathode, springs)
- ② O-Ring
- ③ Mesh frame
- ④ Readout panel (readout strips, Kapton foil with sputtered resistive pattern, connectors...)

On the **experimental** side...

➤ Single processes can not be measured directly

→ Spectrum of the signals induced by γ from Cu-X-Ray

→ Position of the K_α -Peak (and Ar-Escape-Peak)



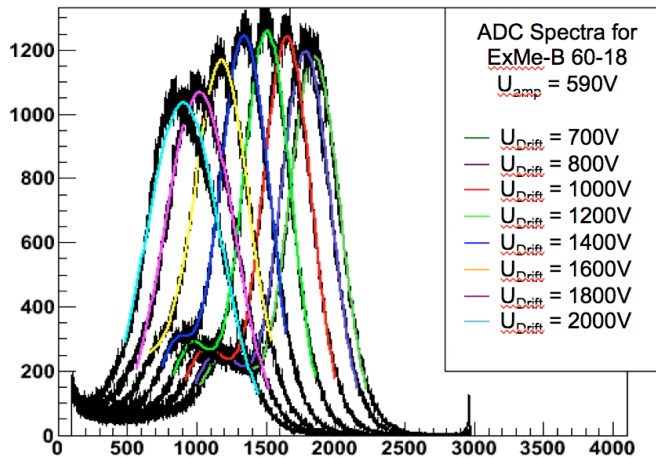
➤ Disentangling a single process (3) requires control and stabilization of all other

$$S = n_{e_{\text{primary}}} \cdot (1 - A) \cdot T \cdot G \cdot C_{\text{readout}} \cdot C_{\text{Signal processing}}$$

1
2
3
4
5

→ $S \propto T$ **underlying assumption**

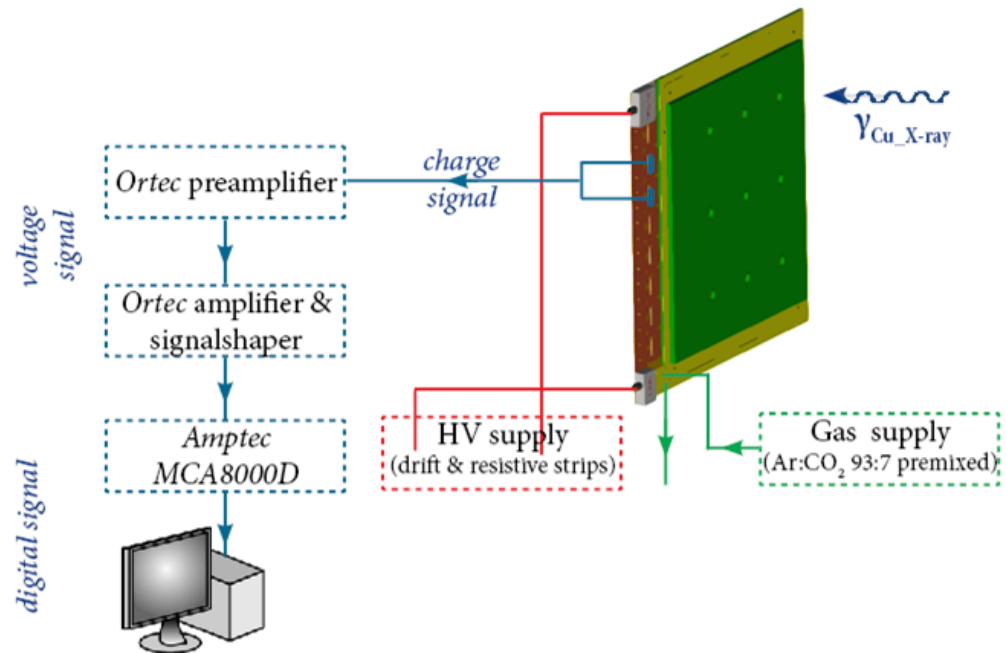
S = Signal (measured in ADC counts), A = fraction of electrons lost to attachment, G = Gain per electron

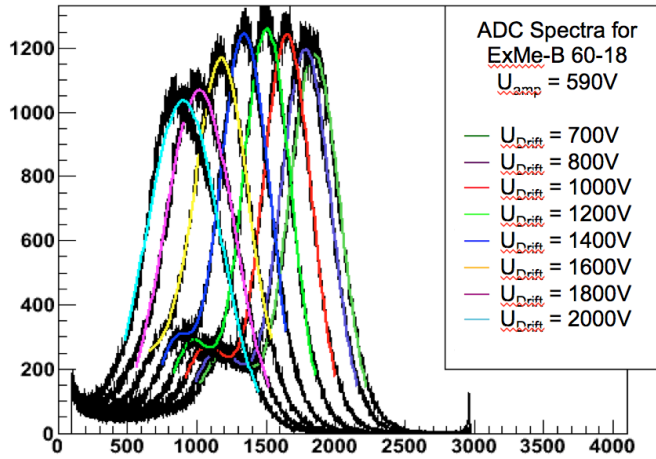


- **Variation of the drift voltage** causes a systematic shift of the spectrum, and accordingly the K_{α} -Peak
 - signal loss corresponds to a loss of amplified e^{-}
 - caused by decreased Transparency with increasing U_{drift}
(increase of mean energy for electrons approaching the mesh)
- Presented during IWAD & 14th RD51 Meeting (2014, Kolkata)

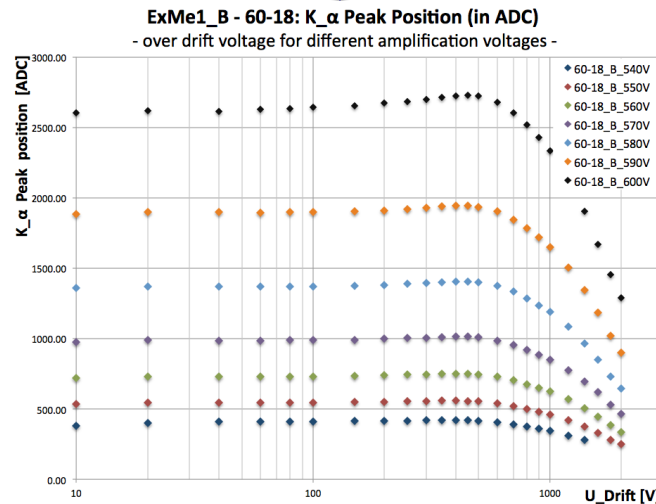
Intense Measurement program (Jan/Feb):

- 3 Spectra each $\approx 3 \cdot 10^5$ events
- screening U_{Drift} : 10V – 2000V (over 5mm)
- for different U_{amp} : 540V – 600V (over 128 μ m)
- repeated in each Sector A,B,C & D:
 - 5, 7, 8.5 & 10mm pillar distance
- with 4 different meshes:
 - 45-18, 60-18, 50-30, 71-30
- ≈ 10.000 spectra recorded





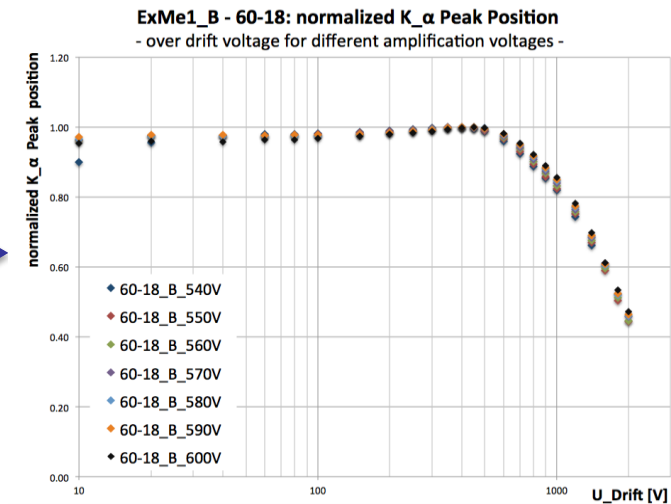
K_α -Peak Position
over U_{Drift}



- Spectra are fitted with a two-gauss-function (K_α - & Esc peak) (K_β and its contribution to the Esc peak are not (jet) considered)
- Each K_α -Peak position corresponds to one point in the 'Transparency' curve
- Normalizing the curves corrects for all proportional factors (Normalization to 1, from expectation of 100% Transparency for ideal E-field settings)

Normalization to
Maximum = 1

→ Transparency

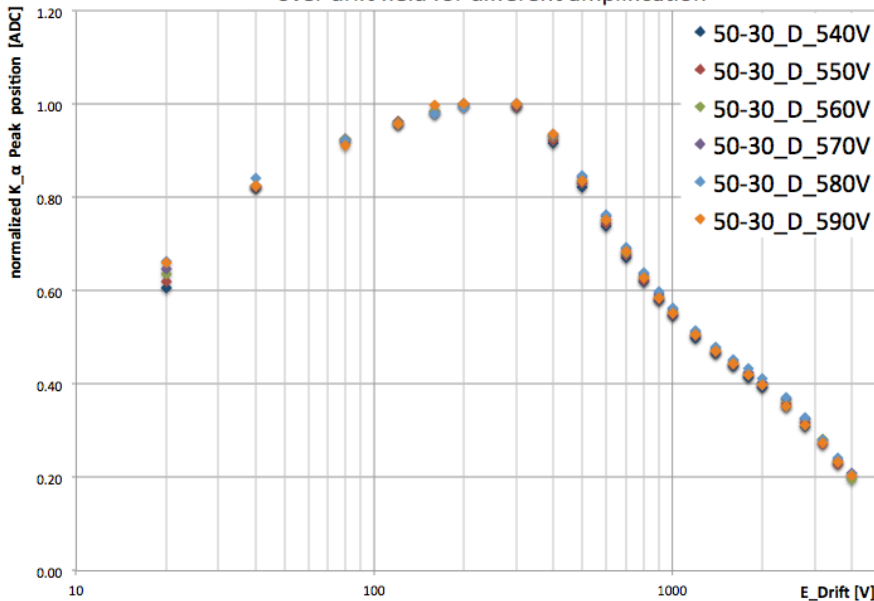


- T is assumed to be dependent from the electrical fields on **both** sides of the mesh:

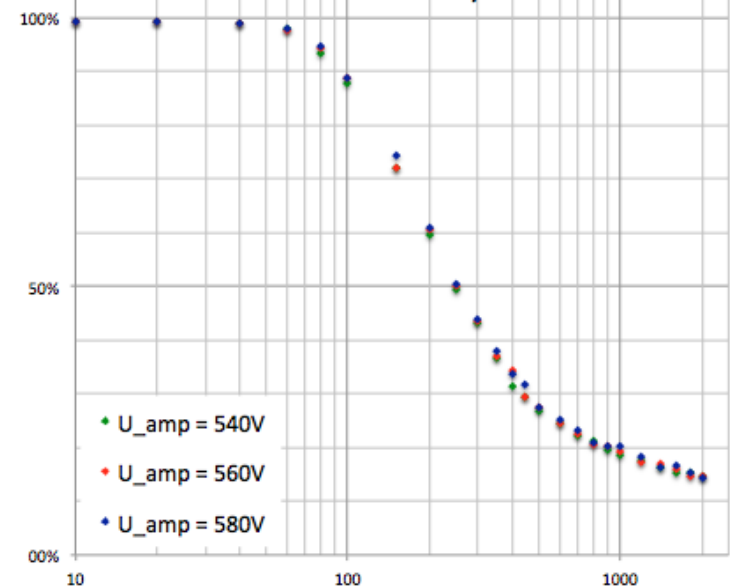
$$\cancel{T(E_{drift}/E_{amp})} \quad \rightarrow \quad \cancel{T(E_{drift}; E_{amp})} \quad \rightarrow \quad T(E_{drift})$$

- Data taken over **the full working-range** of the MM (540V - 600V \rightarrow 42,2kV/cm - 46,9kV/cm) shows very small dependence (<2% effect) of T on U_{amp} .

ExMe1_D - 50-30: normalized K_{α} Peak Position (in ADC)
- over drift field for different amplification -



Transparency Mesh 50-30 at different U_{amp}
-Simulation only-

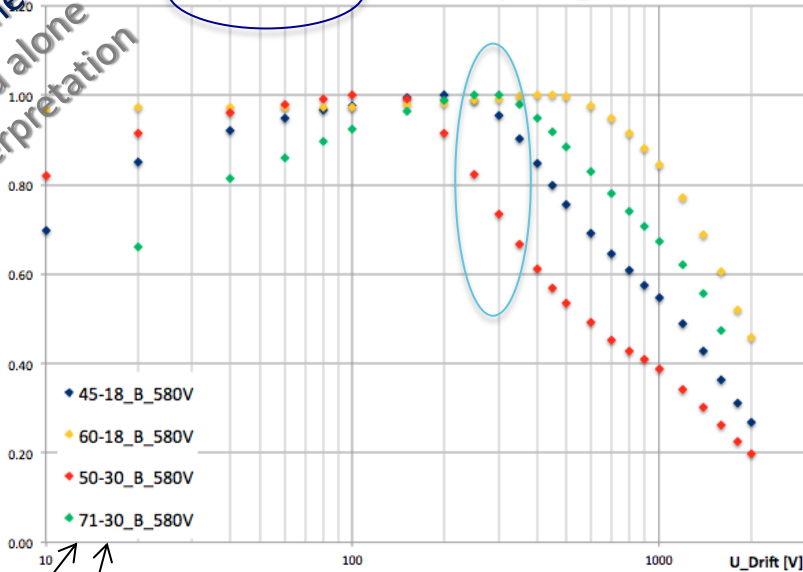


- Simulation with different U_{amp} confirms this results (small systematic deviation at \approx 1% level).

Comparing the **experimental** results for **different meshes**:

ExMe1_B - different meshes: normalized K_α Peak Position
- Exp [norm: 1] - over drift voltage for U_{amp} = 580V -

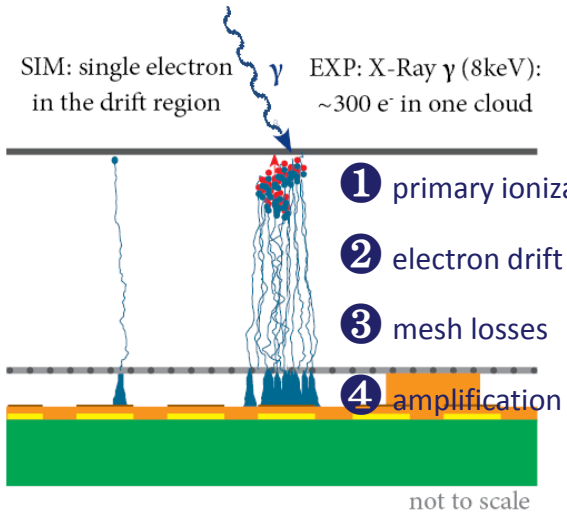
Experiment
'stand alone'
interpretation



mesh-opening
&
wire-diameter
[μm]

Mesh	T U _{drift} =300V
45-18	95,5%
60-18	99,3%
50-30	73,6%
71-30	100,0%

On the **simulation** side...

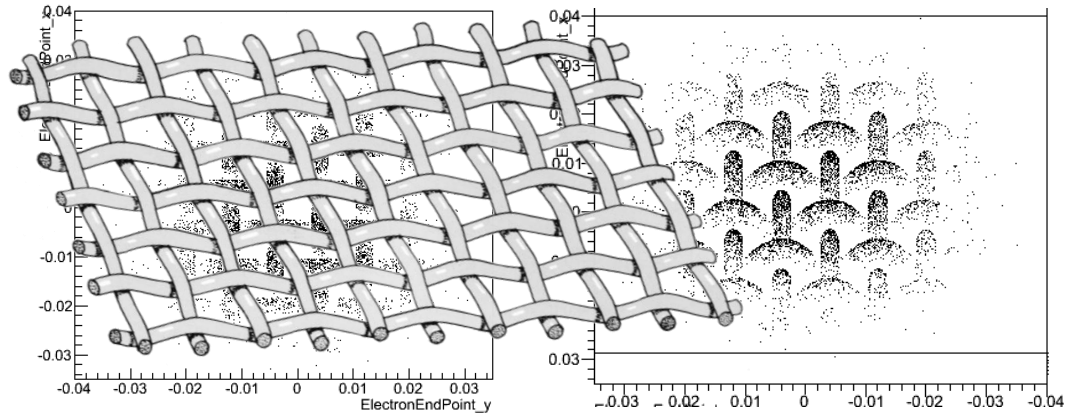
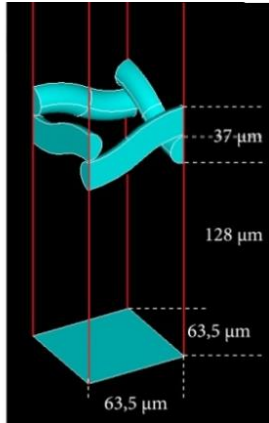
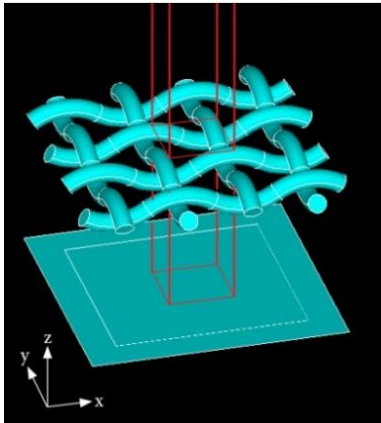


- Full simulation of e.g. a single 8keV- γ -event (by chaining the simulation of all processes) is extremely CPU intensive
- Single process simulation is more reasonable (statistics)

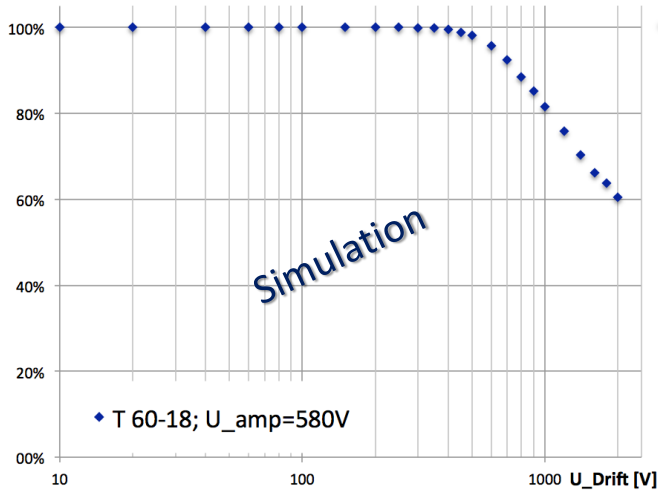
To simulate the mesh transition ③:

- the geometry has been modeled and the **electrical field** calculated using **FEM** (Ansys, > 50.000 elements / unit cell)
- **electron microscopic tracking** performed in Garfield++
- Electron end points yield **T**

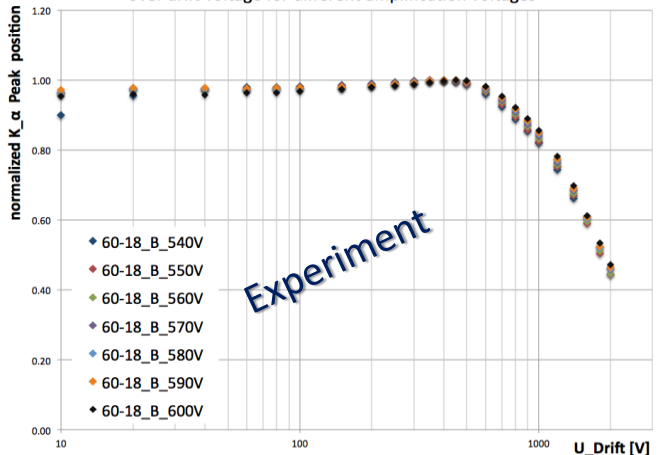
$$T = \frac{\#e^- \text{ passing trough the mesh}}{\#e^- \text{ approaching the mesh}}$$



Simulated Transparency Mesh 60-18

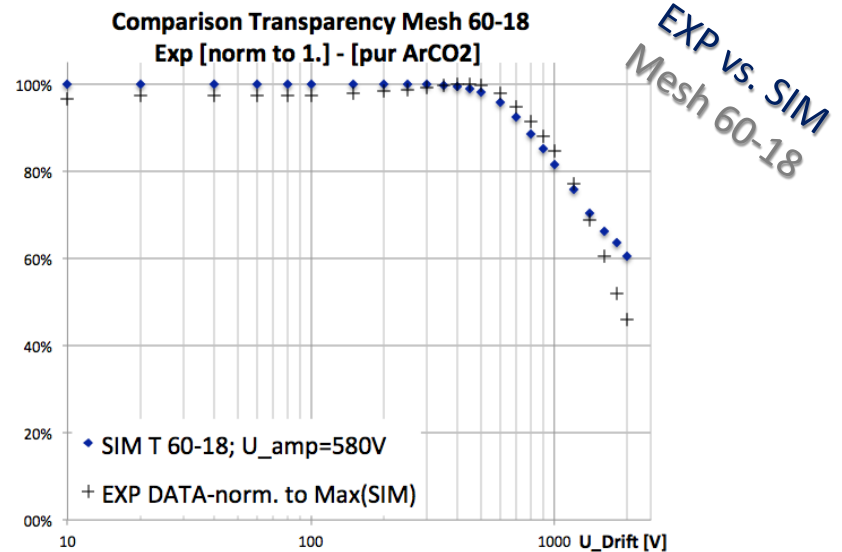


ExMe1_B - 60-18: normalized K_α Peak Position
- over drift voltage for different amplification voltages -

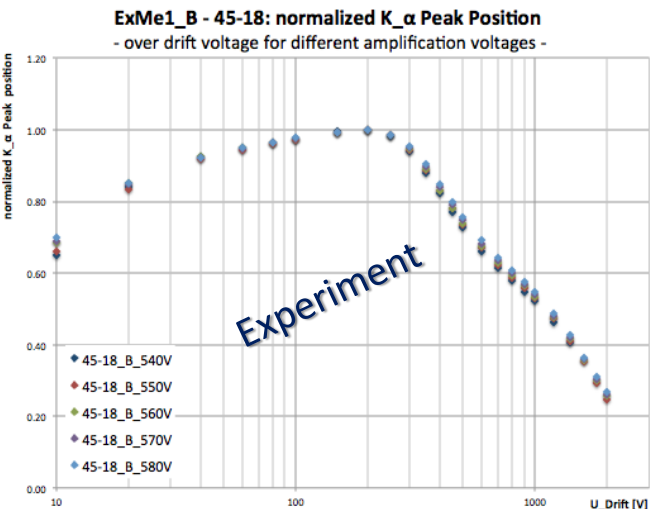
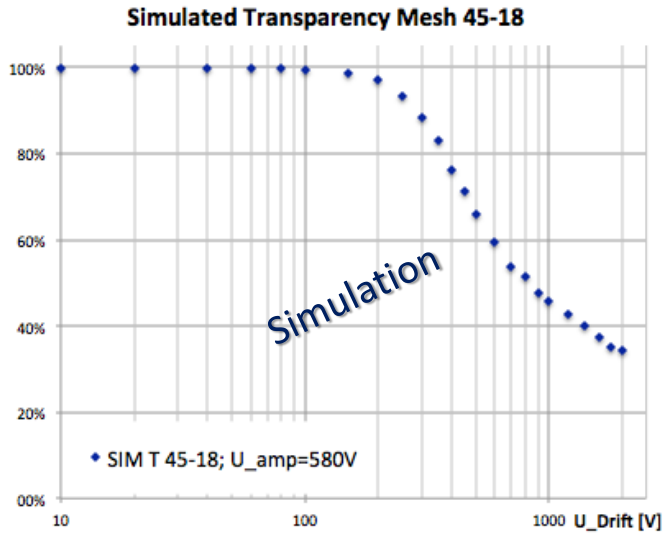


Comparing **simulation** and **experimental** results reveals:

✓ Good agreement in the overall T estimation

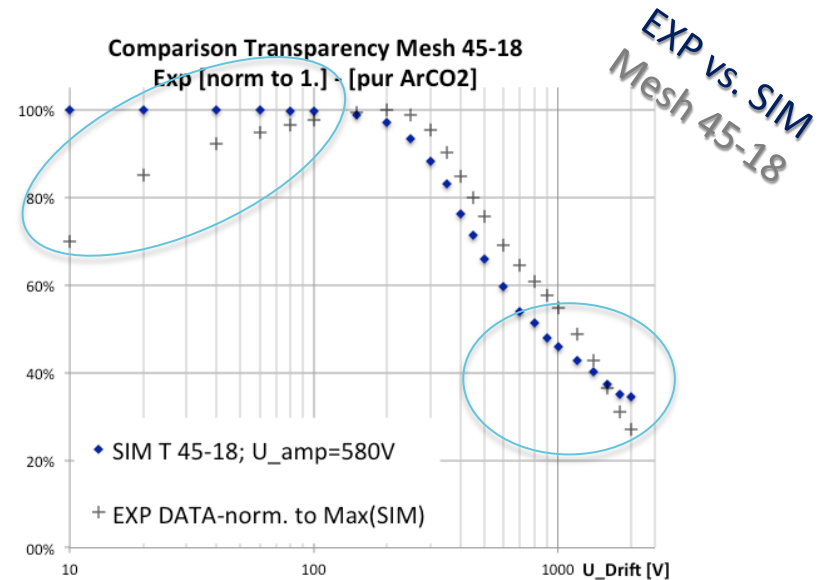


✗ Systematic deviations at the low and high drift field region



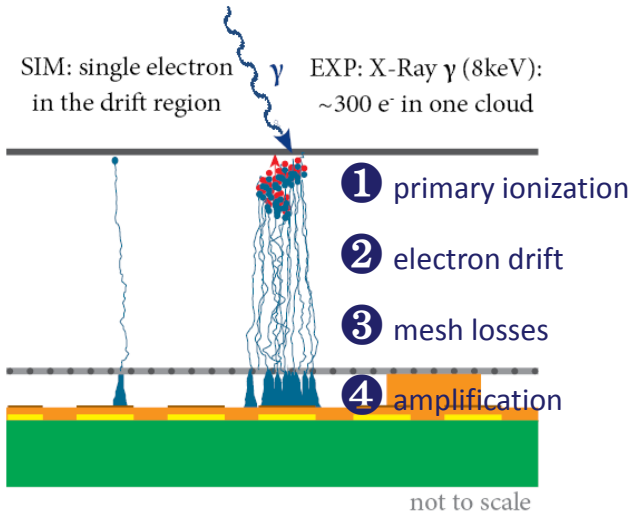
More pronounced discrepancies with other Exp data:

✗ Agreement looks less convincing



✗ Systematic deviations at the low drift field are much more pronounced

✗ Same 'crossing' of simulated and experimental data is observable at high U_{Drift}



Reviewing the underlying assumption

~~$S \propto T$~~

rejected

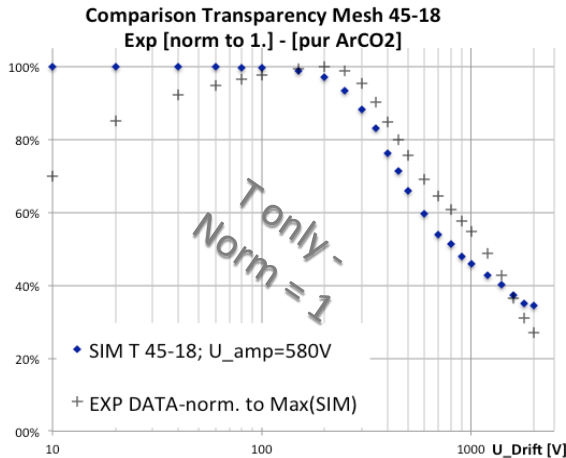


$S \propto (1 - A) \cdot T$

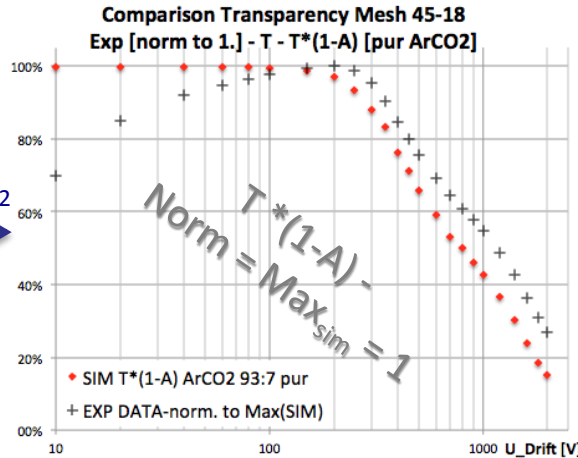
revised assumption

Simulation of the attachment losses during electron drift (2) :

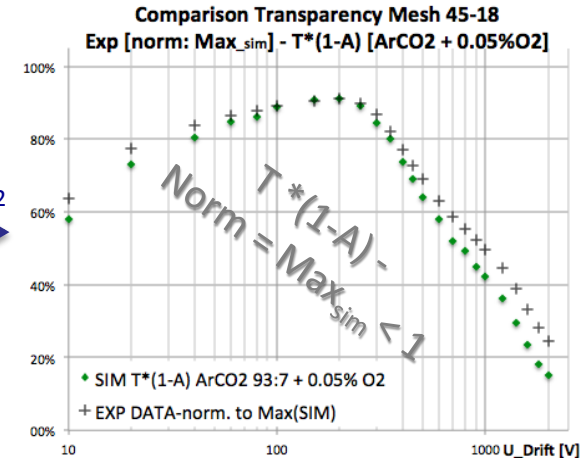
- non-negligible attachment to CO_2 at high e^- energy
- crucial effect of small gas impurities ($< + 0.1 \% O_2$) at low U_{Drift}



$+CO_2$
 \rightarrow



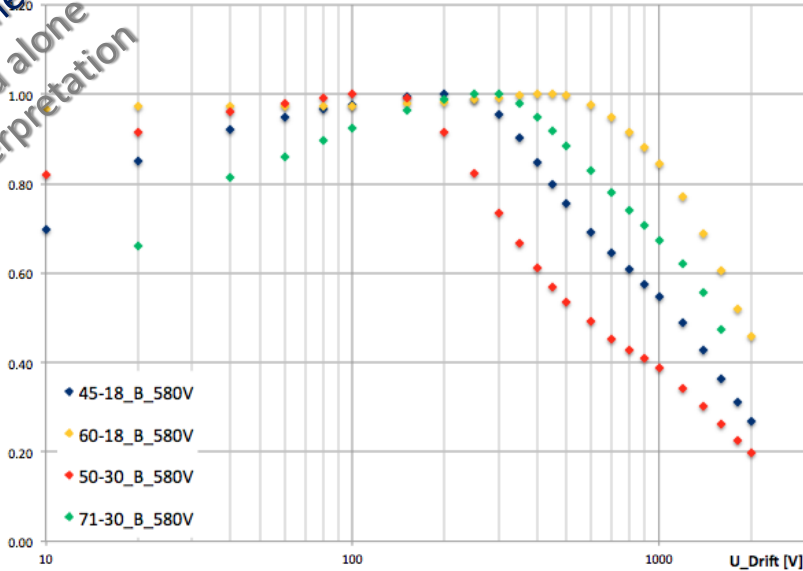
$+O_2$
 \rightarrow



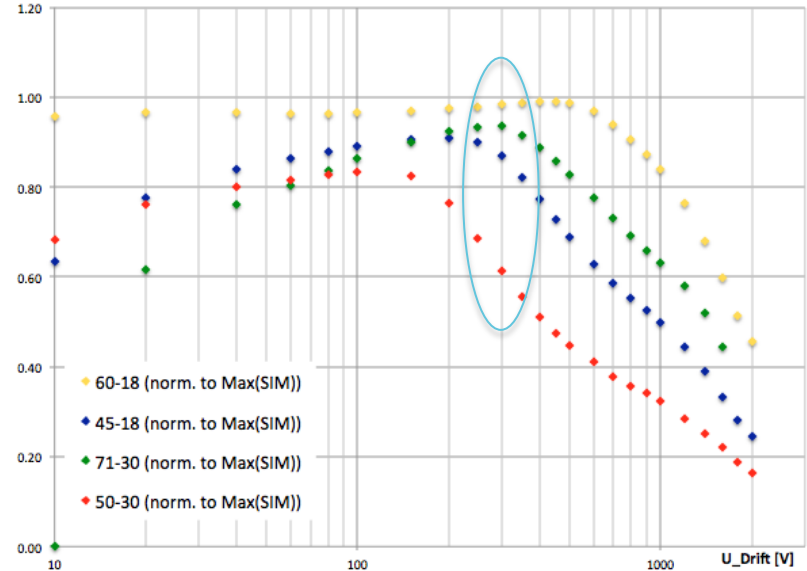
Comparing the experimental data under interpretation of simulation results:

Experiment
'stand alone'
interpretation

ExMe1_B - different meshes: normalized K_{α} Peak Position
- Exp [norm: 1] - over drift voltage for $U_{amp} = 580V$ -



ExMe1_B - different meshes: normalized K_{α}
Exp [norm: Max_sim] - $T*(1-A)$ [ArCO₂ + 0.0x%O₂]



Mesh	$T U_{drift}=300V$
45-18	95,5%
60-18	99,3%
50-30	73,6%
71-30	100,0%

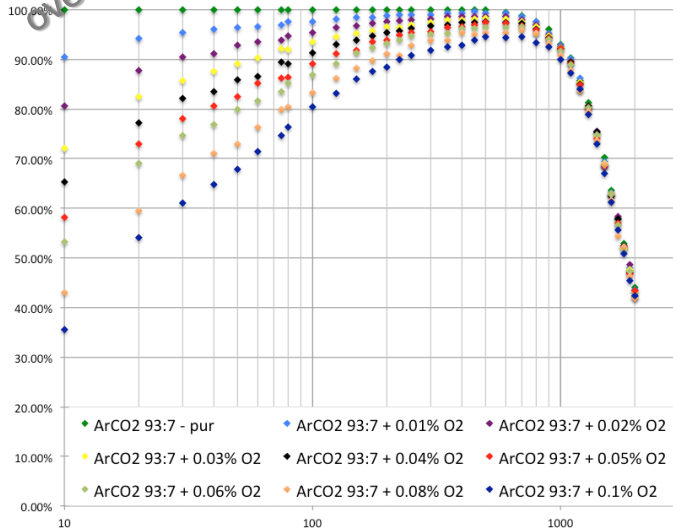
Mesh	$T*(1-A) U_{drift}=300V$
45-18	86,9%
60-18	98,4%
50-30	61,3%
71-30	93,4%

Problem: Oxygen-Impurities in <0,1% concentration varies during hours / days

→ Different curves / data taken must be individually matched to the right concentrations

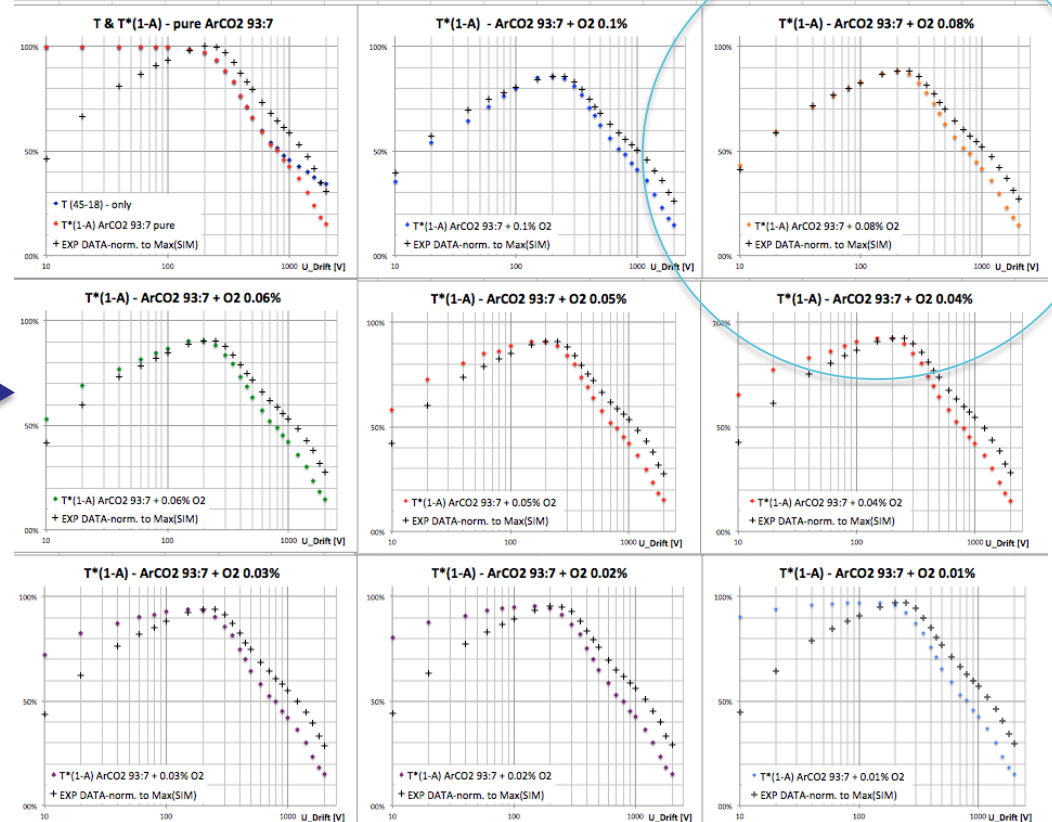
*Simulation
Attachment losses
over 5mm drift*

1 - Attachment after 5mm Drift
in ArCO2 93:7 + different % O2

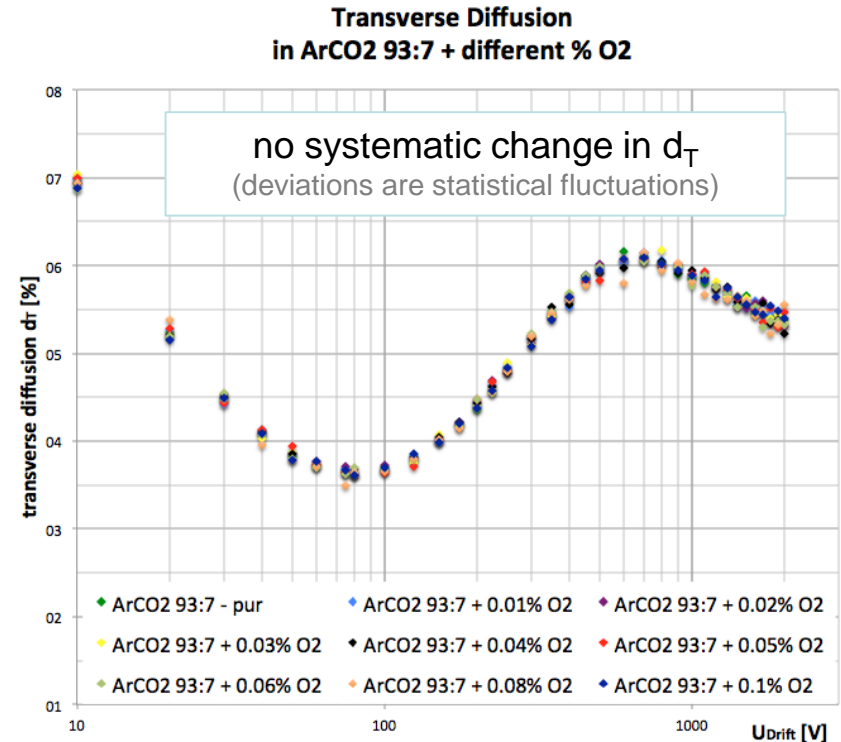
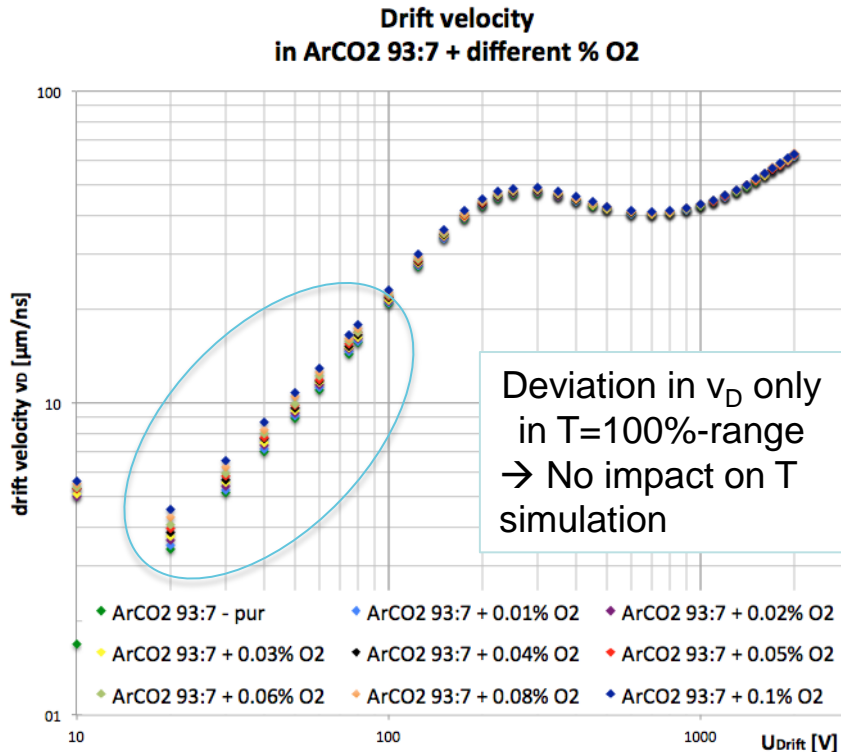


Effective Transparency: $T^*(1-A)$ - ExMe1_45-18_A

(Simulation comparison with Experiment - Experimental data normalized to Max_sim)



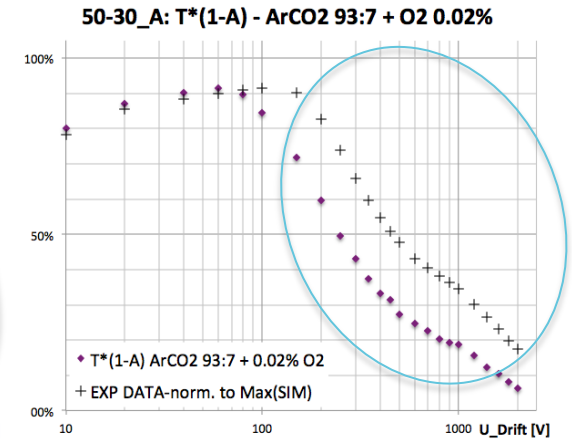
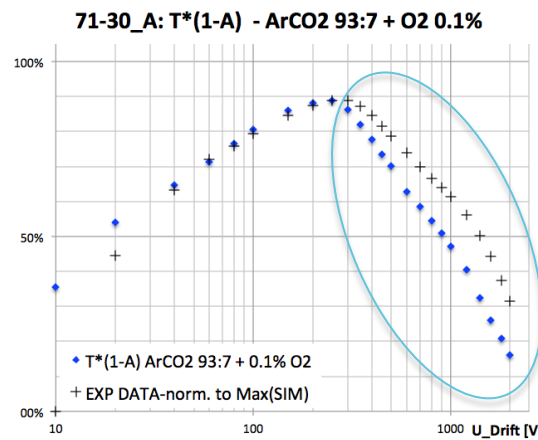
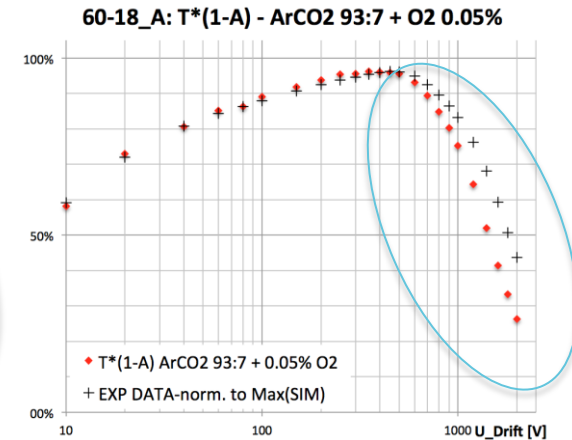
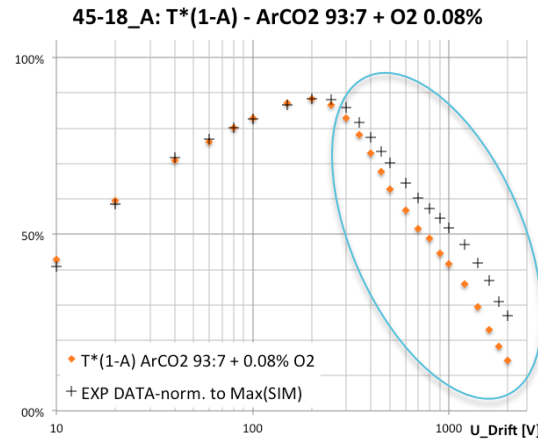
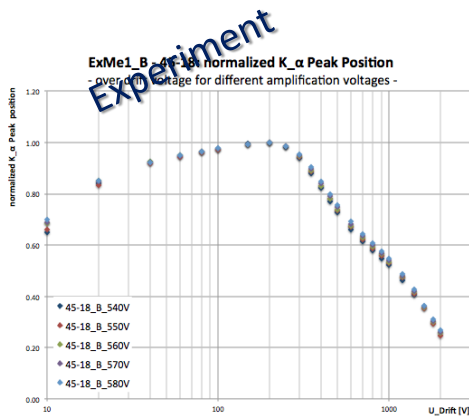
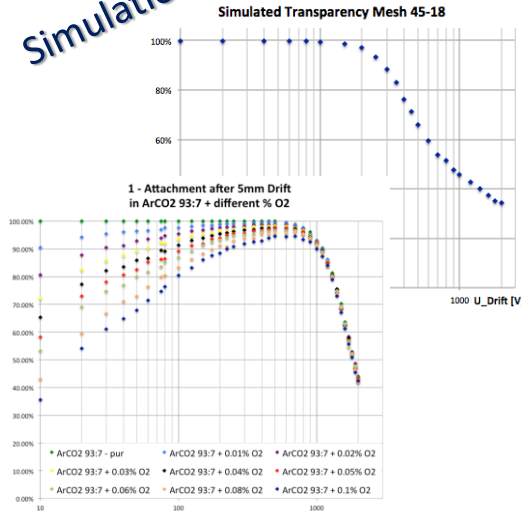
Follow-up question: Does this tiny (<0.1%) O₂ impurity effect the gas properties sufficiently to influence transparency simulations (simulated with pure ArCO₂ 93:7) ?



→ **No 'adjusted' Transparency simulation (due to tiny O₂ impurities) necessary!**

✓ Convincing overall agreement for all meshes

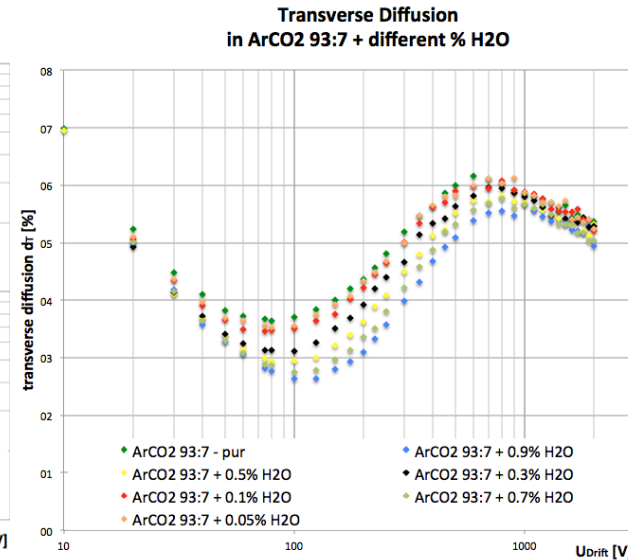
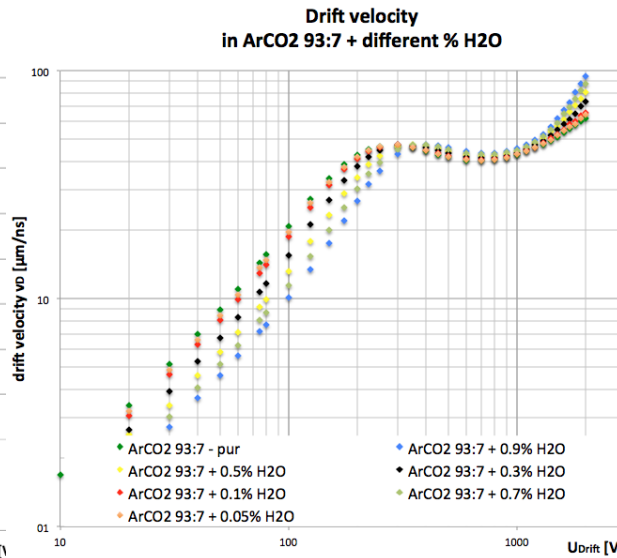
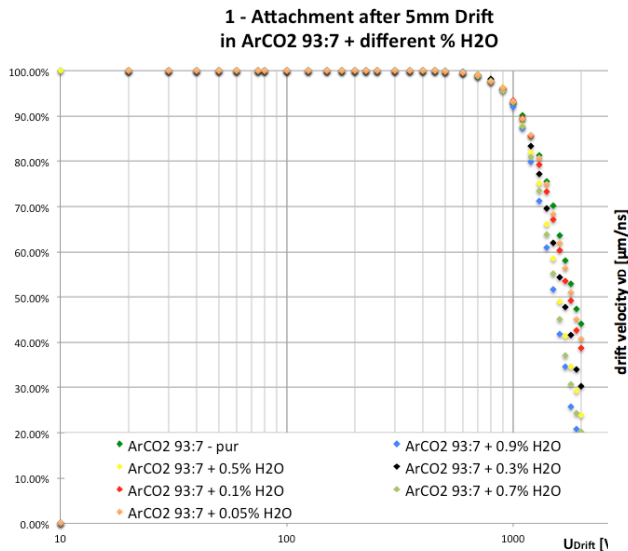
Simulation



✗ Still systematic deviations

→ other gas impurities(H₂O ...) ? Exp? Sim?

Simulating impact of H₂O contamination (very recent results!):



Higher H₂O concentrations (<1%) increase attachment at high U_{Drift} ...

... and have significant impact on v_D and d_T

→ Adjusted Simulation of T necessary?

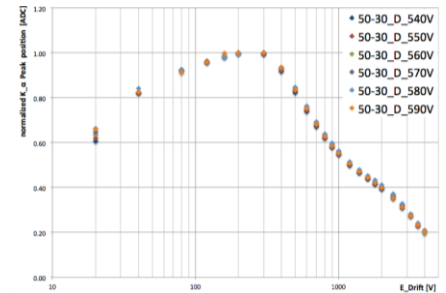
→ Verify/ reject H₂O concentration in experiment

→ **Tiny H₂O impurities are unlikely to cause the visible systematic effect!**

→ Further possible contaminants to be studied

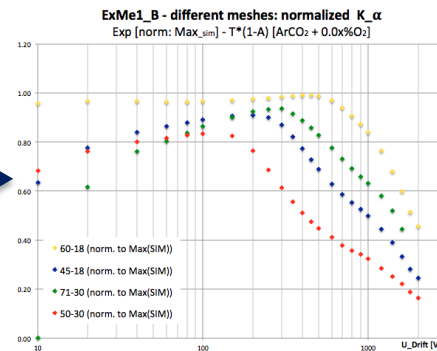
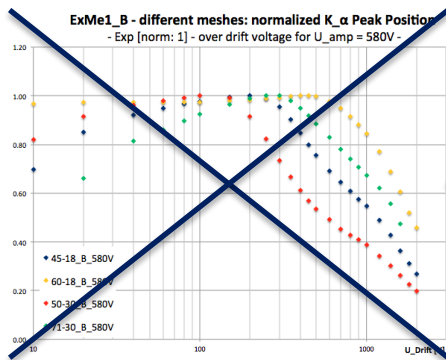
- Experimental data & simulation show little effect of **amplification voltages U_{amp}** on the transparency

$$\cancel{T(E_{drift}; E_{amp})} \rightarrow T(E_{drift})$$



- Measured ‘effective transparency’ \neq mesh transparency

Double-checking experimental assumptions (and data interpretation) by correct modeling & simulation is crucial



Mesh	EXP: $T _{U_{drift}=300V}$	EXP & SIM: $T * (1-A) _{U_{drift}=300V}$
45-18	95,5%	86,9%
60-18	99,3%	98,4%
50-30	73,6%	61,3%
71-30	100,0%	93,4%

- Identification of further ‘impurity-effects’ is ongoing (H_2O , N_2 , $H_2...$)
- Next measurements should be done with an improved gas-system and within shorter time periods

Sincere thanks to...

You
- for your attention -

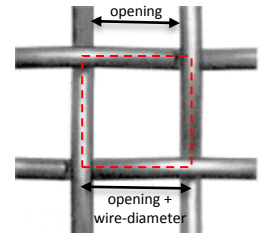
- Rui de Oliveira and the CERN PCB workshop for final design and of production of the Exchangeable Mesh Micromegas prototype
- the CERN GDD Laboratory, in particular Patrik Thuiner & Eraldo Oliveri for their support during the experimental set-up, data-acquisition and –analysis
- Rob Veenhof for fruitful discussions on simulation details

BACKUP

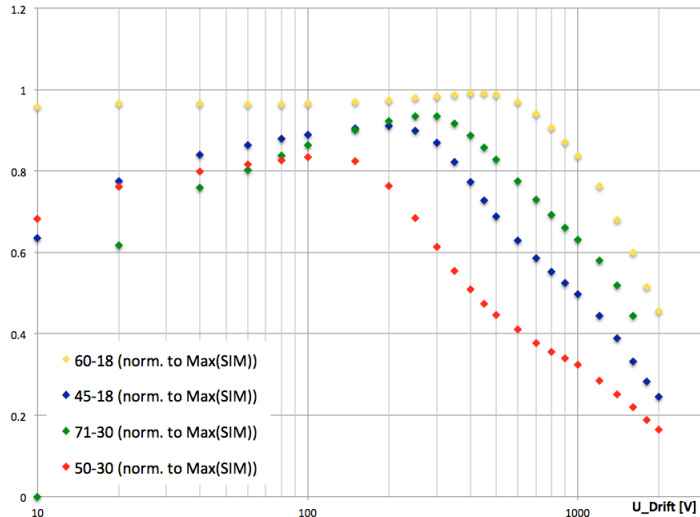
The open area of a mesh is assumed to be a good predictor for the transparency

$$\left(\frac{\text{opening}}{\text{opening} + d_{\text{wire}}} \right)^2$$

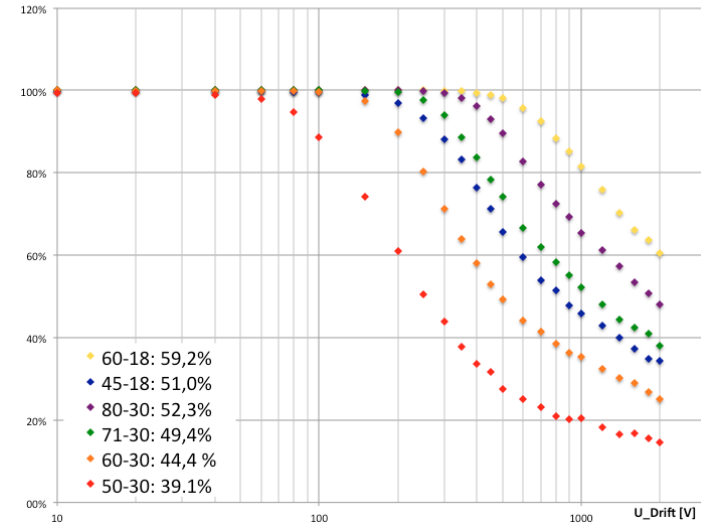
- However: Simulation shows deviation from the rule
higher open area → *better transparency*,
when comparing meshes with different wire diameters.



ExMe1_B - different meshes: normalized K_{α}
Exp [norm: Max_{sim}] - T*(1-A) [ArCO₂ + 0.0x%O₂]



Simulated Transparency - different meshes - all



- Experimental Data confirms this 'order' of mesh transparencies (≠ order of open area)

Drift panel

- with internal gas distribution and HV conduct
- mounted on honeycomb + FR4 stiff-back
- carrying springs pressing down the mesh frame

O-ring

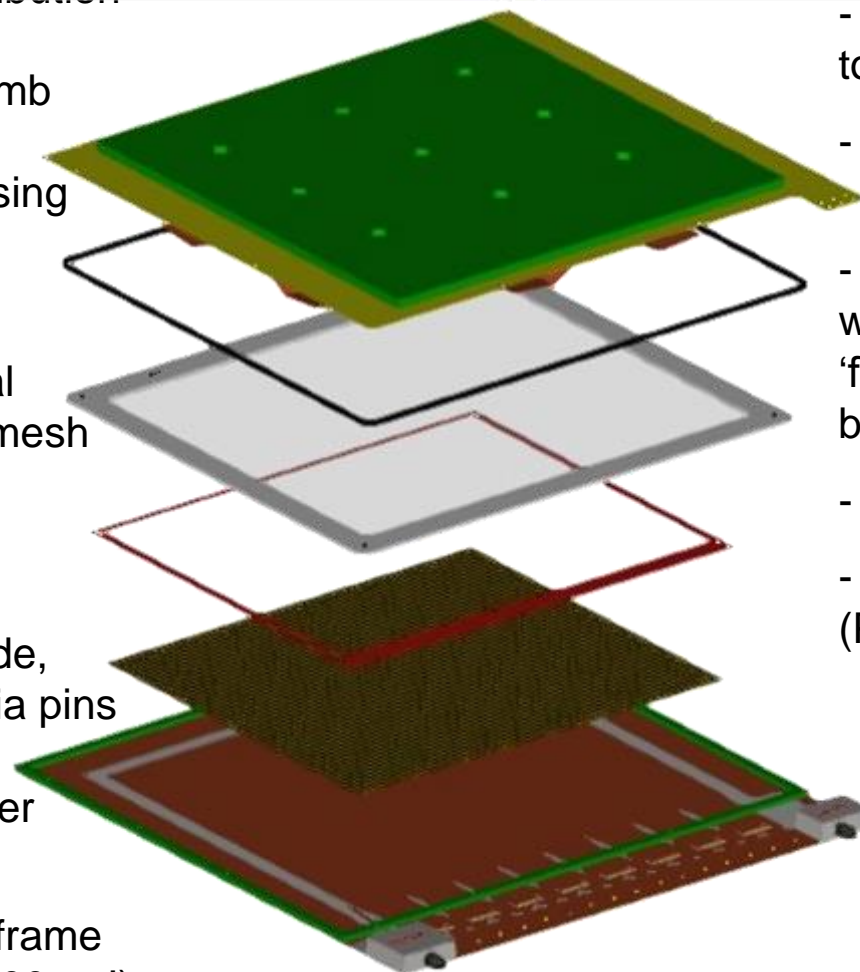
placed between external FR4 frame (5mm) and mesh frame (4mm+springs)

Mesh frame

Mesh glued on lower side, aligned with r/o board via pins in the corner.

Ground contact to copper ground on r/o plane.

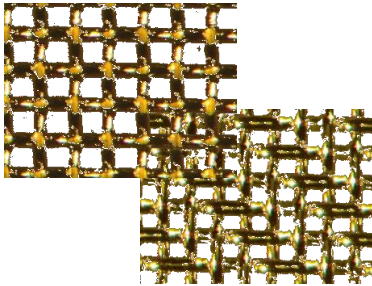
(! Non-flatness of the frame due to mesh tension $\sim 500\mu\text{m}$!)



Readout panel

- copper readout strips routed to Panasonic connectors
- Kapton™ foil with sputtered resistive pattern
- cover lay (128 μm pyralux) with pillar structure and 'frame' to define mesh boarder height
- glued outer FR4 frame
- connectors for HV, r/o (Panasonic) and grounding

- A variety of **mesh specification** details can be studied:



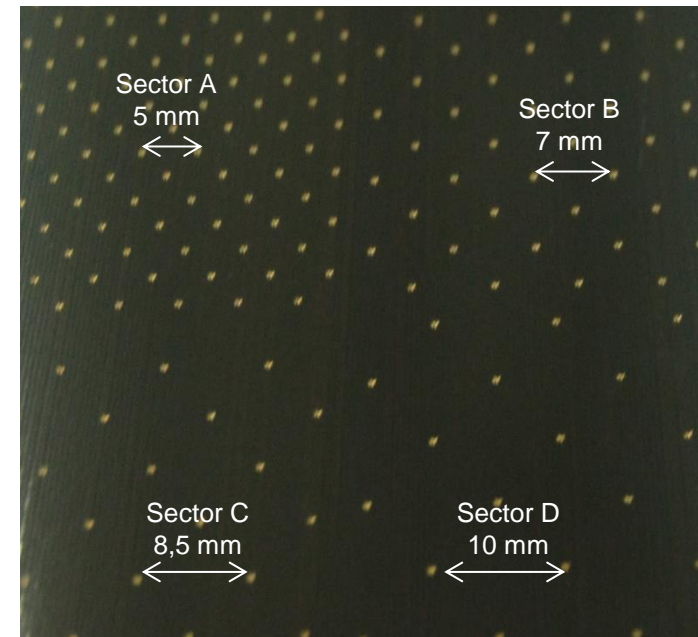
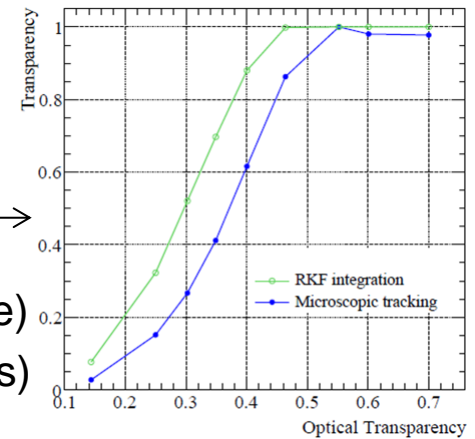
- different wire diameter
- different openings with same wires
- no/ soft / strong calendared meshes
- different types of weaving (plain vs. twill weave)
- alternative mesh material (metalized synthetics)

→ First measurements show the severe impact of mesh geometry on gain behavior

- The ExMe readout is divided in four sectors, covered **by different spaced pillar** patterns. (Pillar-arrangement in regular triangles with different side-length between 5-10mm)

→ Impact on gain behavior is observed

- Second ExMe chamber is available, where the **sputtered resistive layer** is replaced by a **screen-printed** one.



Backup – ExMe results: Influence of pillar pattern on gain

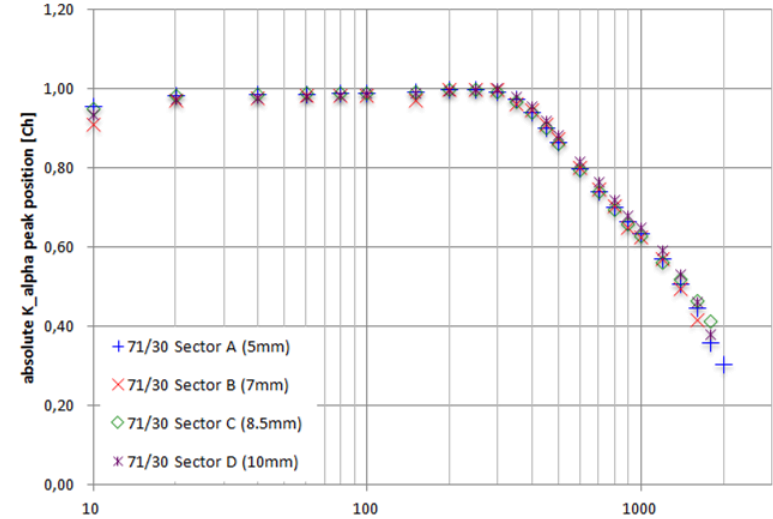
Transparency is (as expected) not depended on the supporting pillar pattern / distances.

→ Difference in inactive area are discarded during normalization to T_{max}

The mean gain on the contrary is effected:

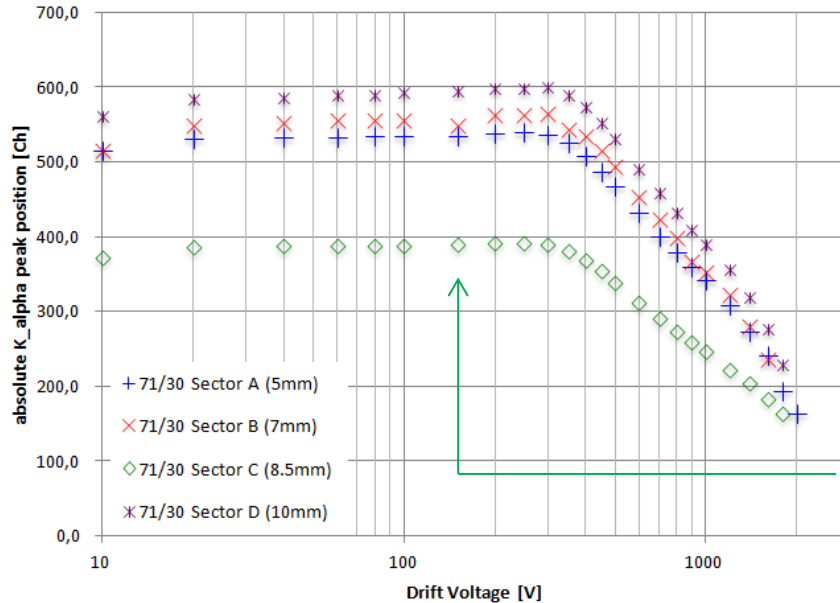
Transparency Scan - ExMe - 71/30 - Sector comparison

($E_{amp} = 580V$ fixed, E_{drift} varied)



K_alpha Peak position - ExMe - 71/30 - Sector comparison

($E_{amp} = 580V$ fixed, E_{drift} varied)



Greater pillar distance leads to higher mean gain (10-15%)

→ Larger pillar distance leads to higher sagging of the mesh between pillars (<math><1\mu\text{m}</math> at 5mm few, $\sim 2\mu\text{m}$ with 10mm)
→ Yielding a lower effective amplification gap
Leading at this working point to higher gain

Deviating behavior in one spot
→ Hint to non-flatness in the r/o or deviation in the pillar height

Drift Voltage [V]

Gain over amplification gap size - log/log
(Garfield++ Simulation, parallel plate approximation)

